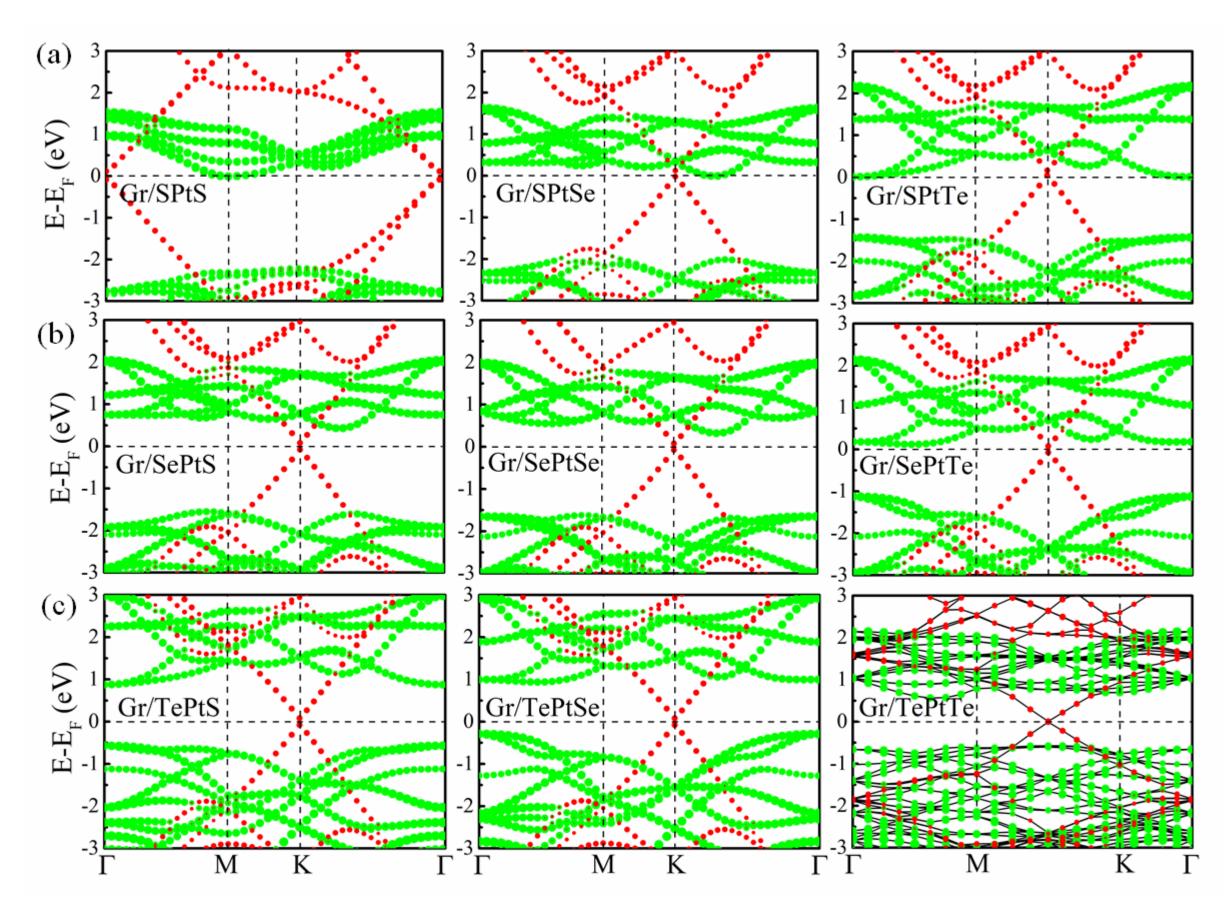
## Interface dependence of electrical contact and graphene doping in graphene/XPtY (X, Y = S, Se, Te) heterostructures

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**Fig. S1** The projected band structures of the Gr/XPtY systems based on HSE06 hybrid functional method. The green and red lines stand for the contribution of XPtY layer and Gr, respectively. (a) The Gr/SPtY systems. (b) The Gr/SePtY systems. (c) The Gr/TePtY systems.